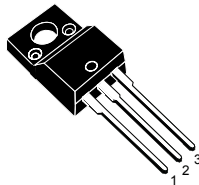
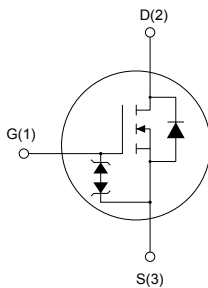


N-channel 650 V, 275 mΩ typ., 12 A MDmesh M2 Power MOSFET in a TO-220FP ultra narrow leads package



TO-220FP
ultra narrow leads



AM01476v1



Product status link

[STFU18N65M2](#)

Product summary

Order code	STFU18N65M2
Marking	18N65M2
Package	TO-220FP ultra narrow leads
Packing	Tube

Features

Order code	V_{DS}	$R_{DS(on) \text{ max.}}$	I_D
STFU18N65M2	650 V	330 mΩ	12 A

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- Very low turn-off switching losses
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	650	V
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	12	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	8	
$I_{DM}^{(1)}$	Drain current (pulsed)	48	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	25	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$, $T_C = 25\text{ }^\circ\text{C}$)	2.5	kV
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature range	-55 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range		$^\circ\text{C}$

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 12\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS}(\text{peak}) < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.
3. $V_{DD} = 520\text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	5	$^\circ\text{C}/\text{W}$
R_{thJA}	Thermal resistance, junction-to-ambient	62.5	$^\circ\text{C}/\text{W}$

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max.)	2	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	450	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	650	-	-	V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$	-	-	1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_C = 125\text{ °C}^{(1)}$	-	-	100	
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$	-	-	± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 6\text{ A}$	-	275	330	$\text{m}\Omega$

1. Specified by design, not tested in production.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	770	-	pF
C_{oss}	Output capacitance		-	35	-	pF
C_{rss}	Reverse transfer capacitance		-	1.2	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0\text{ V}$	-	175	-	pF
R_g	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	6.1	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 12\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see the Figure 14. Test circuit for gate charge behavior)	-	20	-	nC
Q_{gs}	Gate-source charge		-	3.6	-	nC
Q_{gd}	Gate-drain charge		-	8.5	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 6\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	11	-	ns
t_r	Rise time		-	7.5	-	ns
$t_{d(off)}$	Turn-off delay time	(see the Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	46	-	ns
t_f	Fall time		-	12.5	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-	-	12	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-	-	48	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 12\text{ A}$, $V_{GS} = 0\text{ V}$	-	-	1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see the Figure 15. Test circuit for inductive load switching and diode recovery times)	-	331	-	ns
Q_{rr}	Reverse recovery charge		-	3.4	-	μC
I_{RRM}	Reverse recovery current		-	20.5	-	A
t_{rr}	Reverse recovery time	$I_{SD} = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see the Figure 15. Test circuit for inductive load switching and diode recovery times)	-	462	-	ns
Q_{rr}	Reverse recovery charge		-	4.6	-	μC
I_{RRM}	Reverse recovery current		-	20	-	A

1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

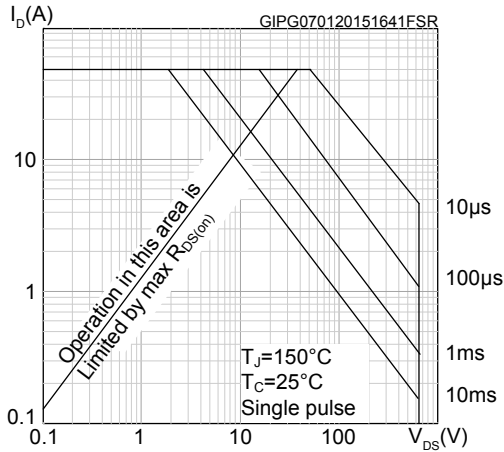
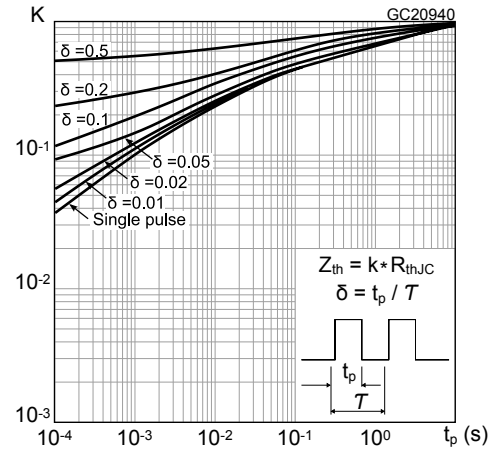
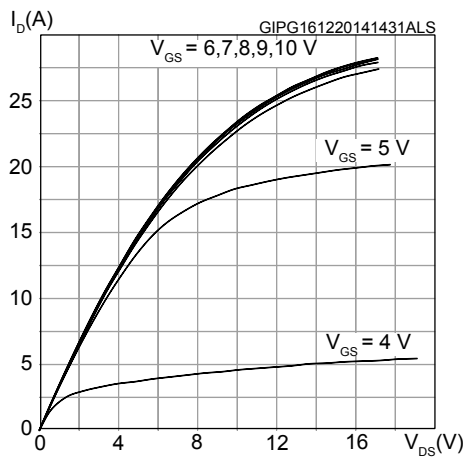
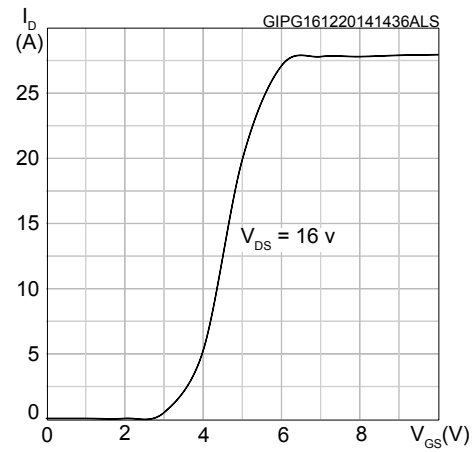
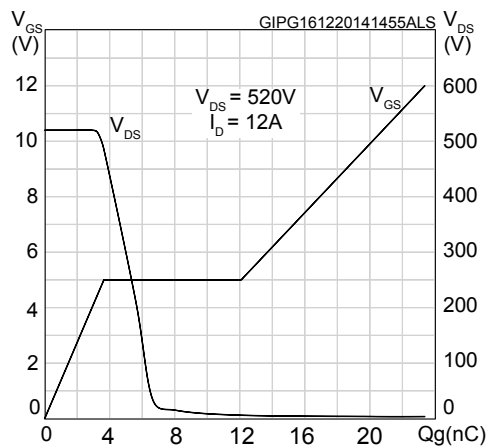
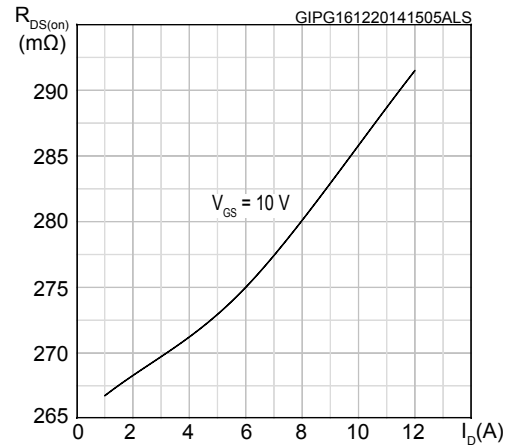
Figure 1. Safe operating area

Figure 2. Normalized transient thermal impedance

Figure 3. Typical output characteristics

Figure 4. Typical transfer characteristics

Figure 5. Typical gate charge characteristics

Figure 6. Typical drain-source on-resistance


Figure 7. Typical capacitance characteristics

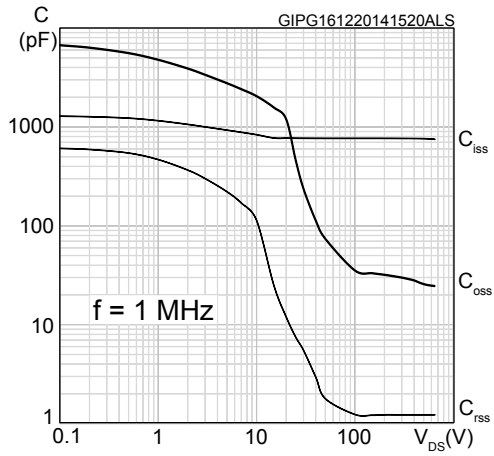


Figure 8. Typical output capacitance stored energy

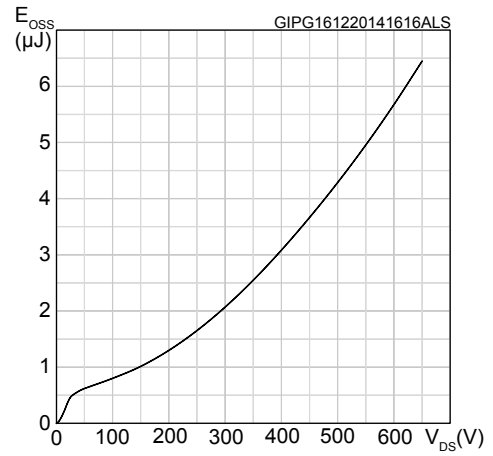


Figure 9. Normalized gate threshold vs temperature

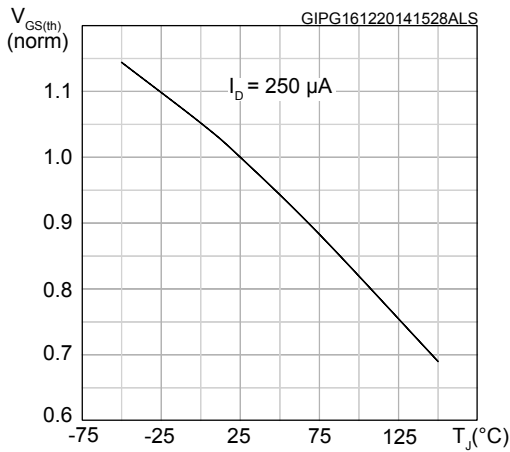


Figure 10. Normalized on-resistance vs temperature

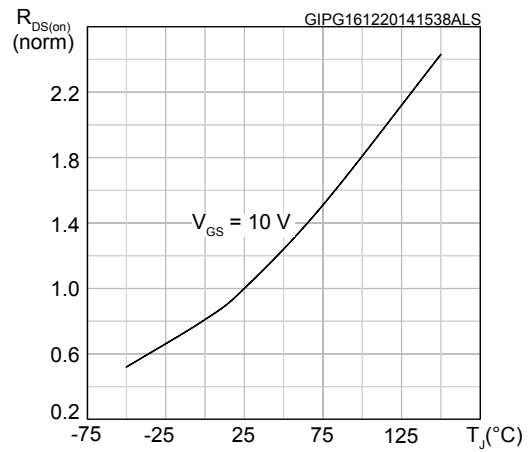


Figure 11. Normalized breakdown voltage vs temperature

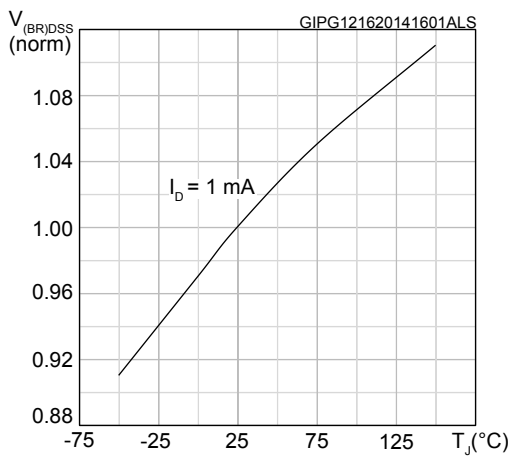
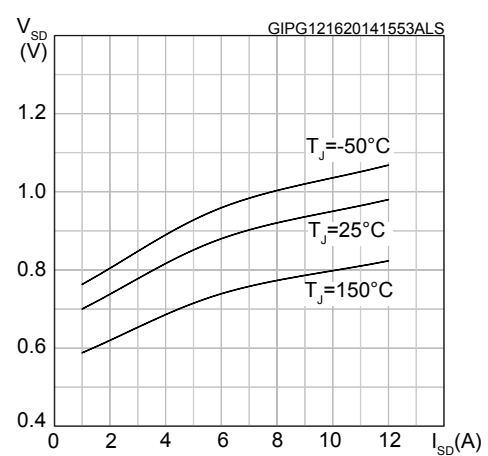


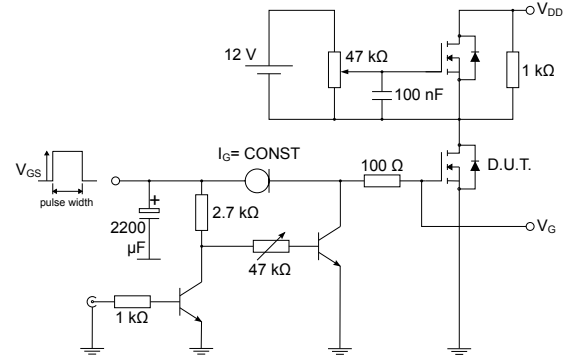
Figure 12. Typical reverse diode forward characteristics



3 Test circuits

Figure 13. Test circuit for resistive load switching times

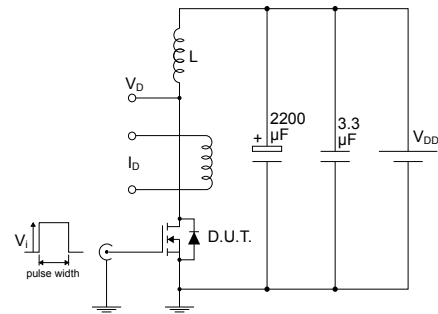

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Figure 14. Test circuit for gate charge behavior


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Figure 15. Test circuit for inductive load switching and diode recovery times

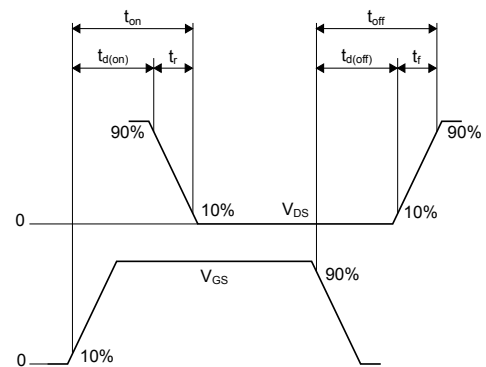

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Figure 16. Unclamped inductive load test circuit


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Figure 17. Unclamped inductive waveform


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Figure 18. Switching time waveform


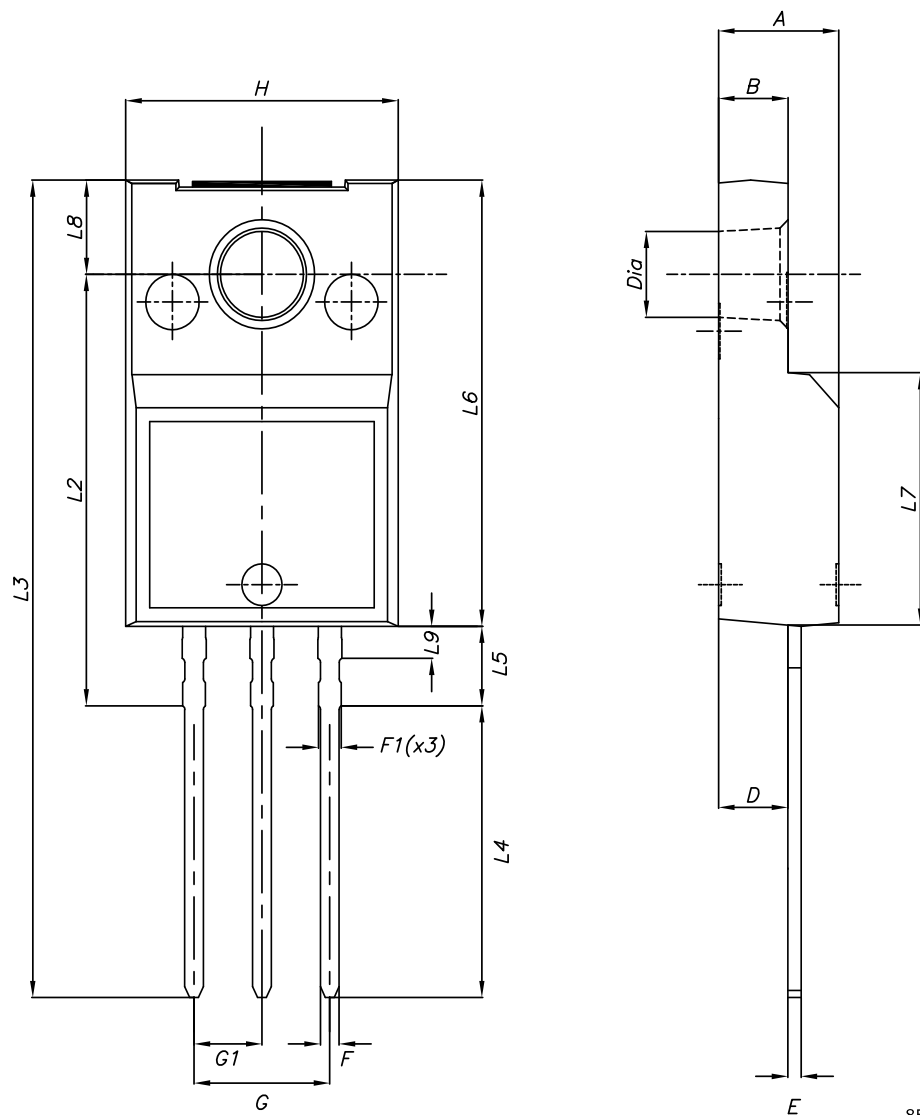
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4 Package information

To meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP ultra narrow leads package information

Figure 19. TO-220FP ultra narrow leads package outline



8576148_3

Table 8. TO-220FP ultra narrow leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
E	0.45		0.60
F	0.65		0.75
F1	-		0.90
G	4.95		5.20
G1	2.40	2.54	2.70
H	10.00		10.40
L2	15.10		15.90
L3	28.50		30.50
L4	10.20		11.00
L5	2.50		3.10
L6	15.60		16.40
L7	9.00		9.30
L8	3.20		3.60
L9	-		1.30
Dia.	3.00		3.20

Revision history

Table 9. Document revision history

Date	Revision	Changes
05-Mar-2015	1	First release.
07-Oct-2015	2	Document status promoted from preliminary to production data.
15-Apr-2026	3	Updated Section 4: Package information . Minor text changes.

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